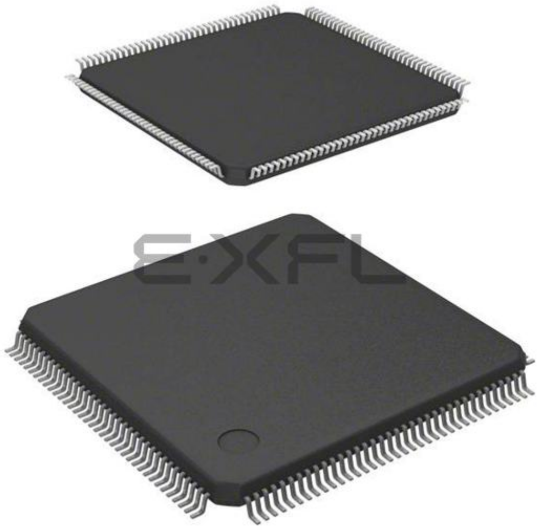


What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	120MHz
Connectivity	CANbus, Ethernet, I²C, IrDA, LINbus, Memory Card, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I²S, LCD, POR, PWM, WDT
Number of I/O	114
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	132K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 24x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	144-LQFP
Supplier Device Package	144-LQFP (20x20)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f217zgt6

Table 7. STM32F21x pin and ball definitions (continued)

Pins					Pin name (function after reset)[1]	Pin type	I / O structure	Note	Alternate functions	Additional functions
LQFP64	LQFP100	LQFP144	LQFP176	UFBGA176						
54	83	116	144	D12	PD2	I/O	FT	-	TIM3_ETR,UART5_RX SDIO_CMD, DCMI_D11, EVENTOUT	-
-	84	117	145	D11	PD3	I/O	FT	-	FSMC_CLK,USART2_CTS, EVENTOUT	-
-	85	118	146	D10	PD4	I/O	FT	-	FSMC_NOE,USART2_RTS, EVENTOUT	-
-	86	119	147	C11	PD5	I/O	FT	-	FSMC_NWE,USART2_TX, EVENTOUT	-
-	-	120	148	D8	V_{SS}	S		-	-	-
-	-	121	149	C8	V_{DD}	S		-	-	-
-	87	122	150	B11	PD6	I/O	FT	-	FSMC_NWAIT,USART2_RX, EVENTOUT	-
-	88	123	151	A11	PD7	I/O	FT	-	USART2_CK,FSMC_NE1, FSMC_NCE2, EVENTOUT	-
-	-	124	152	C10	PG9	I/O	FT	-	USART6_RX, FSMC_NE2,FSMC_NCE3, EVENTOUT	-
-	-	125	153	B10	PG10	I/O	FT	-	FSMC_NCE4_1, FSMC_NE3, EVENTOUT	-
-	-	126	154	B9	PG11	I/O	FT	-	FSMC_NCE4_2, ETH_MII_TX_EN, ETH _RMII_TX_EN, EVENTOUT	-
-	-	127	155	B8	PG12	I/O	FT	-	FSMC_NE4, USART6_RTS, EVENTOUT	-
-	-	128	156	A8	PG13	I/O	FT	-	FSMC_A24, USART6_CTS, ETH_MII_TXD0, ETH_RMII_TXD0, EVENTOUT	-
-	-	129	157	A7	PG14	I/O	FT	-	FSMC_A25, USART6_TX, ETH_MII_TXD1, ETH_RMII_TXD1, EVENTOUT	-
-	-	130	158	D7	V_{SS}	S	-	-	-	-
-	-	131	159	C7	V_{DD}	S	-	-	-	-

Table 9. Alternate function mapping

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF014	AF15
		SYS	TIM1/2	TIM3/4/5	TIM8/9/10/11	I2C1/I2C2/I2C3	SPI1/SPI2/I2S2	SPI3/I2S3	USART1/2/3	UART4/5/ USART6	CAN1/CAN2/ TIM12/13/14	OTG_FS/ OTG_HS	ETH	FSMC/SDIO/ OTG_HS	DCMI		
Port A	PA0-WKUP	-	TIM2_CH1_ETR	TIM 5_CH1	TIM8_ETR	-	-		USART2_CTS	UART4_TX	-	-	ETH_MII_CRS	-	-	-	EVENTOUT
	PA1	-	TIM2_CH2	TIM5_CH2	-	-	-		USART2_RTS	UART4_RX	-	-	ETH_MII _RX_CLK ETH_RMII _REF_CLK	-	-	-	EVENTOUT
	PA2	-	TIM2_CH3	TIM5_CH3	TIM9_CH1	-	-		USART2_TX	-	-	-	ETH_MDIO	-	-	-	EVENTOUT
	PA3	-	TIM2_CH4	TIM5_CH4	TIM9_CH2	-	-		USART2_RX	-	-	OTG_HS_ULPI_D0	ETH _MII_COL	-	-	-	EVENTOUT
	PA4	-	-	-	-	-	SPI1_NSS	SPI3_NSS I2S3_WS	USART2_CK	-	-		-	OTG_HS_SOF	DCMI_HSYNC	-	EVENTOUT
	PA5	-	TIM2_CH1_ETR	-	TIM8_CH1N	-	SPI1_SCK	-	-	-	-	OTG_HS_ULPI_CK	-	-	-	-	EVENTOUT
	PA6	-	TIM1_BKIN	TIM3_CH1	TIM8_BKIN	-	SPI1_MISO	-	-	-	TIM13_CH1	-	-	-	DCMI_PIXCK	-	EVENTOUT
	PA7	-	TIM1_CH1N	TIM3_CH2	TIM8_CH1N	-	SPI1_MOSI	-	-	-	TIM14_CH1	-	ETH_MII _RX_DV ETH_RMII _CRS_DV	-	-	-	EVENTOUT
	PA8	MCO1	TIM1_CH1	-	-	I2C3_SCL	-	-	USART1_CK	-	-	OTG_FS_SOF	-	-	-	-	EVENTOUT
	PA9	-	TIM1_CH2	-	-	I2C3_SMBA	-	-	USART1_TX	-	-		-	-	DCMI_D0	-	EVENTOUT
	PA10	-	TIM1_CH3	-	-	-	-	-	USART1_RX	-	-	OTG_FS_ID	-	-	DCMI_D1	-	EVENTOUT
	PA11	-	TIM1_CH4	-	-	-	-	-	USART1_CTS	-	CAN1_RX	OTG_FS_DM	-	-	-	-	EVENTOUT
	PA12	-	TIM1_ETR	-	-	-	-	-	USART1_RTS	-	CAN1_TX	OTG_FS_DP	-	-	-	-	EVENTOUT
	PA13	JTMS-SWDIO	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENTOUT
	PA14	JTCK-SWCLK	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENTOUT
	PA15	JTDI	TIM 2_CH1 TIM 2_ETR	-	-	-	SPI1_NSS	SPI3_NSS I2S3_WS	-	-	-	-	-	-	-	-	EVENTOUT

Table 9. Alternate function mapping (continued)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF014	AF15
		SYS	TIM1/2	TIM3/4/5	TIM8/9/10/11	I2C1/I2C2/I2C3	SPI1/SPI2/I2S2	SPI3/I2S3	USART1/2/3	UART4/5/ USART6	CAN1/CAN2/ TIM12/13/14	OTG_FS/ OTG_HS	ETH	FSMC/SDIO/ OTG_HS	DCMI		
Port B	PB0	-	TIM1_CH2N	TIM3_CH3	TIM8_CH2N	-	-	-	-	-	-	OTG_HS_ULPI_D1	ETH _MII_RXD2	-	-	-	EVENTOUT
	PB1	-	TIM1_CH3N	TIM3_CH4	TIM8_CH3N	-	-	-	-	-	-	OTG_HS_ULPI_D2	ETH _MII_RXD3	-	-	-	EVENTOUT
	PB2	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENTOUT
	PB3	JTDO/ TRACESWO	TIM2_CH2	-	-	-	SPI1_SCK	SPI3_SCK I2S3_SCK	-	-	-	-	-	-	-	-	EVENTOUT
	PB4	JTRST	-	TIM3_CH1	-	-	SPI1_MISO	SPI3_MISO	-	-	-	-	-	-	-	-	EVENTOUT
	PB5	-	-	TIM3_CH2	-	I2C1_SMBA	SPI1_MOSI	SPI3_MOSI I2S3_SD	-	-	CAN2_RX	OTG_HS_ULPI_D7	ETH _PPS_OUT	-	DCMI_D10	-	EVENTOUT
	PB6	-	-	TIM4_CH1	-	I2C1_SCL	-	-	USART1_TX	-	CAN2_TX	-	-	-	DCMI_D5	-	EVENTOUT
	PB7	-	-	TIM4_CH2	-	I2C1_SDA	-	-	USART1_RX	-	-	-	-	FSMC_NL	DCMI_VSYNC	-	EVENTOUT
	PB8	-	-	TIM4_CH3	TIM10_CH1	I2C1_SCL	-	-	-	-	CAN1_RX	-	ETH _MII_TXD3	SDIO_D4	DCMI_D6	-	EVENTOUT
	PB9	-	-	TIM4_CH4	TIM11_CH1	I2C1_SDA	SPI2_NSS I2S2_WS	-	-	-	CAN1_TX	-	-	SDIO_D5	DCMI_D7	-	EVENTOUT
	PB10	-	TIM2_CH3	-	-	I2C2_SCL	SPI2_SCK I2S2_SCK	-	USART3_TX	-	-	OTG_HS_ULPI_D3	ETH_ MII_RX_ER	-	-	-	EVENTOUT
	PB11	-	TIM2_CH4	-	-	I2C2_SDA	-	-	USART3_RX	-	-	OTG_HS_ULPI_D4	ETH _MII_TX_EN ETH _RMII_TX_EN	-	-	-	EVENTOUT
	PB12	-	TIM1_BKIN	-	-	I2C2_SMBA	SPI2_NSS I2S2_WS	-	USART3_CK	-	CAN2_RX	OTG_HS_ULPI_D5	ETH _MII_TXD0 ETH _RMII_TXD0	OTG_HS_ID	-	-	EVENTOUT
	PB13	-	TIM1_CH1N	-	-	-	SPI2_SCK I2S2_SCK	-	USART3_CTS	-	CAN2_TX	OTG_HS_ULPI_D6	ETH _MII_TXD1 ETH _RMII_TXD1	-	-	-	EVENTOUT
	PB14	-	TIM1_CH2N	-	TIM8_CH2N	-	SPI2_MISO	-	USART3_RTS	-	TIM12_CH1	-	-	OTG_HS_DM	-	-	EVENTOUT
	PB15	RTC_50Hz	TIM1_CH3N	-	TIM8_CH3N	-	SPI2_MOSI I2S2_SD	-	-	-	TIM12_CH2	-	-	OTG_HS_DP	-	-	EVENTOUT

Table 9. Alternate function mapping (continued)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF014	AF15
		SYS	TIM1/2	TIM3/4/5	TIM8/9/10/11	I2C1/I2C2/I2C3	SPI1/SPI2/I2S2	SPI3/I2S3	USART1/2/3	UART4/5/ USART6	CAN1/CAN2/ TIM12/13/14	OTG_FS/ OTG_HS	ETH	FSMC/SDIO/ OTG_HS	DCMI		
Port H	PH0 - OSC_IN	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENTOUT
	PH1 - OSC_OUT	-	-				-	-	-	-	-	-	-	-	-	-	EVENTOUT
	PH2	-	-				-	-	-	-	-	-	ETH _MII_CRS	-	-	-	EVENTOUT
	PH3	-	-				-	-	-	-	-	-	ETH _MII_COL	-	-	-	EVENTOUT
	PH4	-	-			I2C2_SCL	-	-	-	-	-	OTG_HS_ULPI_NXT	-	-	-	-	EVENTOUT
	PH5	-	-			I2C2_SDA	-	-	-	-	-	-	-	-	-	-	EVENTOUT
	PH6	-	-			I2C2_SMBA	-	-	-	-	TIM12_CH1	-	ETH _MII_RXD2	-	-	-	EVENTOUT
	PH7	-	-			I2C3_SCL	-	-	-	-	-	-	ETH _MII_RXD3	-	-	-	EVENTOUT
	PH8	-	-			I2C3_SDA	-	-	-	-	-	-	-	-	DCMI_HSYNC	-	EVENTOUT
	PH9	-	-			I2C3_SMBA	-	-	-	-	TIM12_CH2	-	-	-	DCMI_D0	-	EVENTOUT
	PH10	-	-	TIM5_CH1			-	-	-	-	-	-	-	-	DCMI_D1	-	EVENTOUT
	PH11	-	-	TIM5_CH2			-	-	-	-	-	-	-	-	DCMI_D2	-	EVENTOUT
	PH12	-	-	TIM5_CH3			-	-	-	-	-	-	-	-	DCMI_D3	-	EVENTOUT
	PH13	-	-		TIM8_CH1N		-	-	-	-	CAN1_TX	-	-	-	-	-	EVENTOUT
	PH14	-	-		TIM8_CH2N		-	-	-	-	-	-	-	-	DCMI_D4	-	EVENTOUT
	PH15	-	-		TIM8_CH3N		-	-	-	-	-	-	-	-	DCMI_D11	-	EVENTOUT
Port I	PI0	-	-	TIM5_CH4			SPI2_NSS I2S2_WS	-	-	-	-	-	-	-	DCMI_D13	-	EVENTOUT
	PI1	-	-				SPI2_SCK I2S2_SCK	-	-	-	-	-	-	-	DCMI_D8	-	EVENTOUT
	PI2	-	-		TIM8_CH4		SPI2_MISO	-	-	-	-	-	-	-	DCMI_D9	-	EVENTOUT
	PI3	-	-		TIM8_ETR		SPI2_MOSI I2S2_SD	-	-	-	-	-	-	-	DCMI_D10	-	EVENTOUT
	PI4	-	-		TIM8_BKIN		-	-	-	-	-	-	-	-	DCMI_D5	-	EVENTOUT
	PI5	-	-		TIM8_CH1		-	-	-	-	-	-	-	-	DCMI_VSYNC	-	EVENTOUT
	PI6	-	-		TIM8_CH2		-	-	-	-	-	-	-	-	DCMI_D6	-	EVENTOUT
	PI7	-	-		TIM8_CH3		-	-	-	-	-	-	-	-	DCMI_D7	-	EVENTOUT
	PI8	-	-				-	-	-	-	-	-	-	-	-	-	EVENTOUT
	PI9	-	-				-	-	-	-	CAN1_RX	-	-	-	-	-	EVENTOUT
	PI10	-	-				-	-	-	-	-	-	ETH _MII_RX_ER	-	-	-	EVENTOUT
	PI11	-	-				-	-	-	-	-	OTG_HS_ULPI_DIR	-	-	-	-	EVENTOUT

Table 25. Peripheral current consumption

Peripheral(1)		Typical consumption at 25 °C	Unit
AHB1	GPIO A	0.45	mA
	GPIO B	0.43	
	GPIO C	0.46	
	GPIO D	0.44	
	GPIO E	0.44	
	GPIO F	0.42	
	GPIO G	0.44	
	GPIO H	0.42	
	GPIO I	0.43	
	OTG_HS + ULPI	3.64	
	CRC	1.17	
	BKPSRAM	0.21	
	DMA1	2.76	
	DMA2	2.85	
	ETH_MAC + ETH_MAC_TX ETH_MAC_RX ETH_MAC_PTP	2.99	
AHB2	OTG_FS	3.16	
	DCMI	0.60	
AHB3	FSMC	1.74	
AHB2	CRYPTO	0.39	mA
	HASH	0.50	
	RNG	0.43	

6.3.8 External clock source characteristics

High-speed external user clock generated from an external source

The characteristics given in *Table 27* result from tests performed using an high-speed external clock source, and under ambient temperature and supply voltage conditions summarized in *Table 13*.

Table 27. High-speed external user clock characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSE_ext}	External user clock source frequency[1]	-	1	-	26	MHz
V_{HSEH}	OSC_IN input pin high level voltage		$0.7V_{DD}$	-	V_{DD}	V
V_{HSEL}	OSC_IN input pin low level voltage		V_{SS}	-	$0.3V_{DD}$	
$t_{w(HSE)}$ $t_{w(HSE)}$	OSC_IN high or low time[1]		5	-	-	ns
$t_{r(HSE)}$ $t_{f(HSE)}$	OSC_IN rise or fall time[1]		-	-	20	
$C_{in(HSE)}$	OSC_IN input capacitance[1]	-	-	5	-	pF
$DuCy_{(HSE)}$	Duty cycle	-	45	-	55	%
I_L	OSC_IN Input leakage current	$V_{SS} \leq V_{IN} \leq V_{DD}$	-	-	±1	µA

1. Guaranteed by design, not tested in production.

Low-speed external user clock generated from an external source

The characteristics given in *Table 28* result from tests performed using an low-speed external clock source, and under ambient temperature and supply voltage conditions summarized in *Table 13*.

Table 28. Low-speed external user clock characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{LSE_ext}	User External clock source frequency[1]	-	-	32.768	1000	kHz
V_{LSEH}	OSC32_IN input pin high level voltage		$0.7V_{DD}$	-	V_{DD}	V
V_{LSEL}	OSC32_IN input pin low level voltage		V_{SS}	-	$0.3V_{DD}$	
$t_{w(LSE)}$ $t_{f(LSE)}$	OSC32_IN high or low time[1]		450	-	-	ns
$t_{r(LSE)}$ $t_{f(LSE)}$	OSC32_IN rise or fall time[1]		-	-	50	
$C_{in(LSE)}$	OSC32_IN input capacitance[1]	-	-	5	-	pF
$DuCy_{(LSE)}$	Duty cycle	-	30	-	70	%
I_L	OSC32_IN Input leakage current	$V_{SS} \leq V_{IN} \leq V_{DD}$	-	-	±1	µA

1. Guaranteed by design, not tested in production.

Table 33. Main PLL characteristics (continued)

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Jitter[3]	Cycle-to-cycle jitter	System clock 120 MHz	RMS	-	25	-	ps
			peak to peak	-	±150	-	
	Period Jitter		RMS	-	15	-	
			peak to peak	-	±200	-	
	Main clock output (MCO) for RMII Ethernet	Cycle to cycle at 50 MHz on 1000 samples		-	32	-	
	Main clock output (MCO) for MII Ethernet	Cycle to cycle at 25 MHz on 1000 samples		-	40	-	
	Bit Time CAN jitter	Cycle to cycle at 1 MHz on 1000 samples		-	330	-	
$I_{DD(PLL)}$[4]	PLL power consumption on VDD	VCO freq = 192 MHz VCO freq = 432 MHz		0.15 0.45	-	0.40 0.75	mA
$I_{DDA(PLL)}$[4]	PLL power consumption on VDDA	VCO freq = 192 MHz VCO freq = 432 MHz		0.30 0.55	-	0.40 0.85	mA

1. Take care of using the appropriate division factor M to obtain the specified PLL input clock values. The M factor is shared between PLL and PLLI2S.
2. Guaranteed by design, not tested in production.
3. The use of 2 PLLs in parallel could degraded the Jitter up to +30%.
4. Guaranteed by characterization results, not tested in production.

Table 34. PLLI2S (audio PLL) characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{PLLI2S_IN}	PLLI2S input clock[1]	-	0.95[2]	1	2.10[2]	MHz
f_{PLLI2S_OUT}	PLLI2S multiplier output clock	-	-	-	216	MHz
f_{VCO_OUT}	PLLI2S VCO output	-	192	-	432	MHz
t_{LOCK}	PLLI2S lock time	VCO freq = 192 MHz	75	-	200	µs
		VCO freq = 432 MHz	100	-	300	

The test results are given in *Table 40*. They are based on the EMS levels and classes defined in application note AN1709.

Table 40. EMS characteristics

Symbol	Parameter	Conditions	Level/ Class
V_{FESD}	Voltage limits to be applied on any I/O pin to induce a functional disturbance	V_{DD} = 3.3 V, LQFP176, T_A = +25 °C, f_{HCLK} = 120 MHz, conforms to IEC 61000-4-2	2B
V_{EFTB}	Fast transient voltage burst limits to be applied through 100 pF on V_{DD} and V_{SS} pins to induce a functional disturbance	V_{DD} = 3.3 V, LQFP176, T_A = +25 °C, f_{HCLK} = 120 MHz, conforms to IEC 61000-4-2	4A

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Software recommendations

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical Data corruption (control registers...)

Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the Oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

USB OTG FS characteristics

The USB OTG interface is USB-IF certified (Full-Speed). This interface is present in both the USB OTG HS and USB OTG FS controllers.

Table 55. USB OTG FS startup time

Symbol	Parameter	Max	Unit
$t_{STARTUP}$(1)	USB OTG FS transceiver startup time	1	µs

1. Guaranteed by design, not tested in production.

Table 56. USB OTG FS DC electrical characteristics

Symbol		Parameter	Conditions	Min(1)	Typ	Max(1)	Unit
Input levels	V_{DD}	USB OTG FS operating voltage		3.0(2)	-	3.6	V
	V_{DI}(3)	Differential input sensitivity	I(USB_FS_DP/DM, USB_HS_DP/DM)	0.2	-	-	V
	V_{CM}(3)	Differential common mode range	Includes V_{DI} range	0.8	-	2.5	
	V_{SE}(3)	Single ended receiver threshold		1.3	-	2.0	
Output levels	V_{OL}	Static output level low	R_L of 1.5 kΩ to 3.6 V(4)	-	-	0.3	V
	V_{OH}	Static output level high	R_L of 15 kΩ to V_{SS}(4)	2.8	-	3.6	
R_{PD}		PA11, PA12, PB14, PB15 (USB_FS_DP/DM, USB_HS_DP/DM)	$V_{IN} = V_{DD}$	17	21	24	kΩ
		PA9, PB13 (OTG_FS_VBUS, OTG_HS_VBUS)		0.65	1.1	2.0	
R_{PU}		PA12, PB15 (USB_FS_DP, USB_HS_DP)	$V_{IN} = V_{SS}$	1.5	1.8	2.1	
		PA9, PB13 (OTG_FS_VBUS, OTG_HS_VBUS)	$V_{IN} = V_{SS}$	0.25	0.37	0.55	

1. All the voltages are measured from the local ground potential.
2. The STM32F215xx and STM32F217xx USB OTG FS functionality is ensured down to 2.7 V but not the full USB OTG FS electrical characteristics which are degraded in the 2.7-to-3.0 V V_{DD} voltage range.
3. Guaranteed by design, not tested in production.
4. R_L is the load connected on the USB OTG FS drivers

Table 73. Asynchronous multiplexed PSRAM/NOR read timings[1][2] (continued)

Symbol	Parameter	Min	Max	Unit
$t_{h(Data\_NE)}$	Data hold time after FSMC_NEx high	0	-	ns
$t_{h(Data\_NOE)}$	Data hold time after FSMC_NOE high	0	-	ns

1. C_L = 30 pF.
2. Guaranteed by characterization results, not tested in production.

Figure 58. Asynchronous multiplexed PSRAM/NOR write waveforms

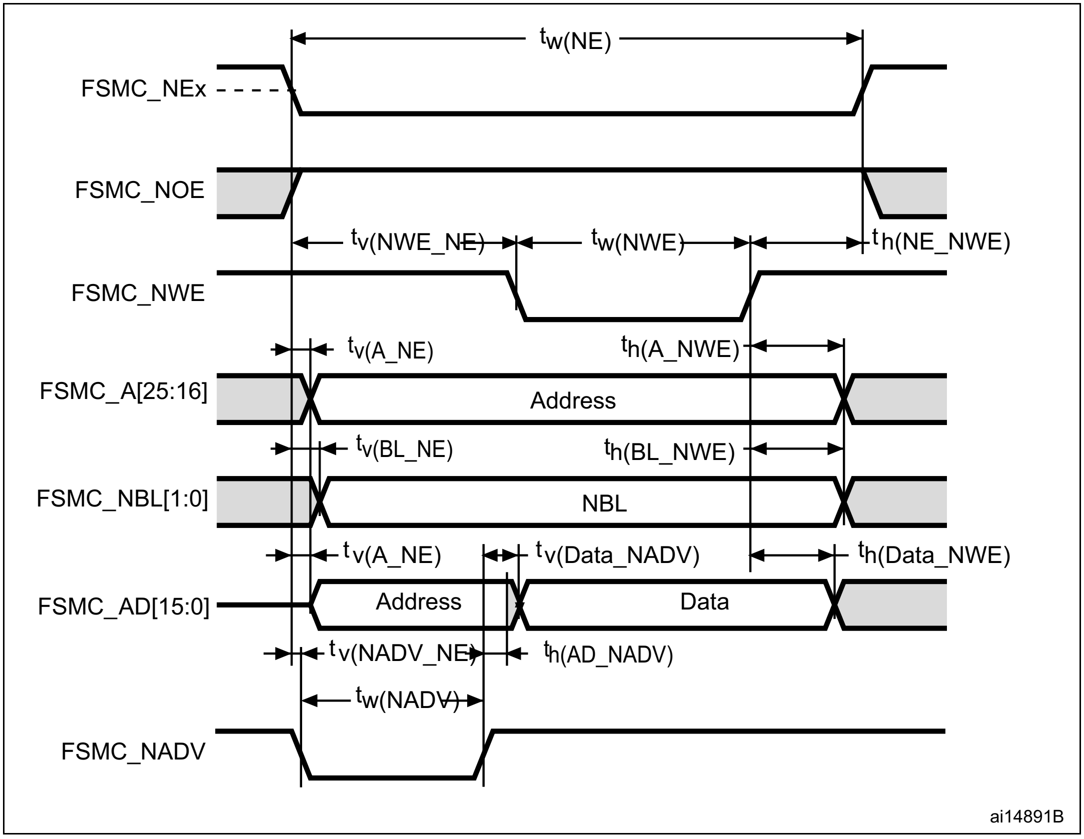


Table 74. Asynchronous multiplexed PSRAM/NOR write timings[1][2]

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FSMC_NE low time	$4T_{HCLK}-1$	$4T_{HCLK}+1$	ns
$t_{v(NWE\_NE)}$	FSMC_NEx low to FSMC_NWE low	$T_{HCLK}- 1$	T_{HCLK}	ns
$t_{w(NWE)}$	FSMC_NWE low tim e	$2T_{HCLK}$	$2T_{HCLK}+1$	ns
$t_{h(NE\_NWE)}$	FSMC_NWE high to FSMC_NE high hold time	$T_{HCLK}- 1$	-	ns
$t_{v(A\_NE)}$	FSMC_NEx low to FSMC_A valid	-	0	ns
$t_{v(NADV\_NE)}$	FSMC_NEx low to FSMC_NADV low	1	2	ns
$t_{w(NADV)}$	FSMC_NADV low time	$T_{HCLK}- 2$	$T_{HCLK}+ 2$	ns
$t_{h(AD\_NADV)}$	FSMC_AD(adress) valid hold time after FSMC_NADV high)	T_{HCLK}	-	ns

Table 76. Synchronous multiplexed PSRAM write timings[1][2] (continued)

Symbol	Parameter	Min	Max	Unit
$t_{d(CLKL-NWEL)}$	FSMC_CLK low to FSMC_NWE low	-	1	ns
$t_{d(CLKL-NWEH)}$	FSMC_CLK low to FSMC_NWE high	0	-	ns
$t_{d(CLKL-ADIV)}$	FSMC_CLK low to FSMC_AD[15:0] invalid	0	-	ns
$t_{d(CLKL-DATA)}$	FSMC_A/D[15:0] valid data after FSMC_CLK low	-	2	ns
$t_{d(CLKL-NBLH)}$	FSMC_CLK low to FSMC_NBL high	0.5	-	ns

1. C_L = 30 pF.
2. Guaranteed by characterization results, not tested in production.

Figure 61. Synchronous non-multiplexed NOR/PSRAM read timings

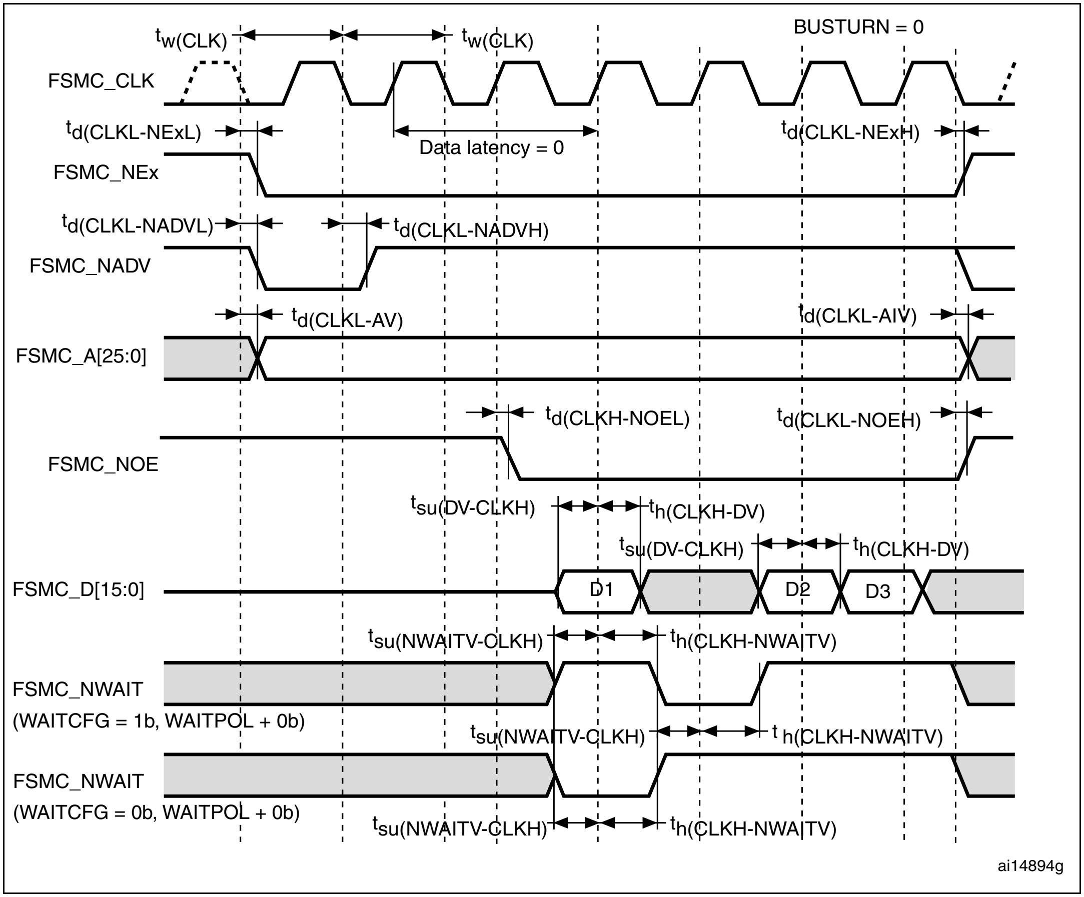
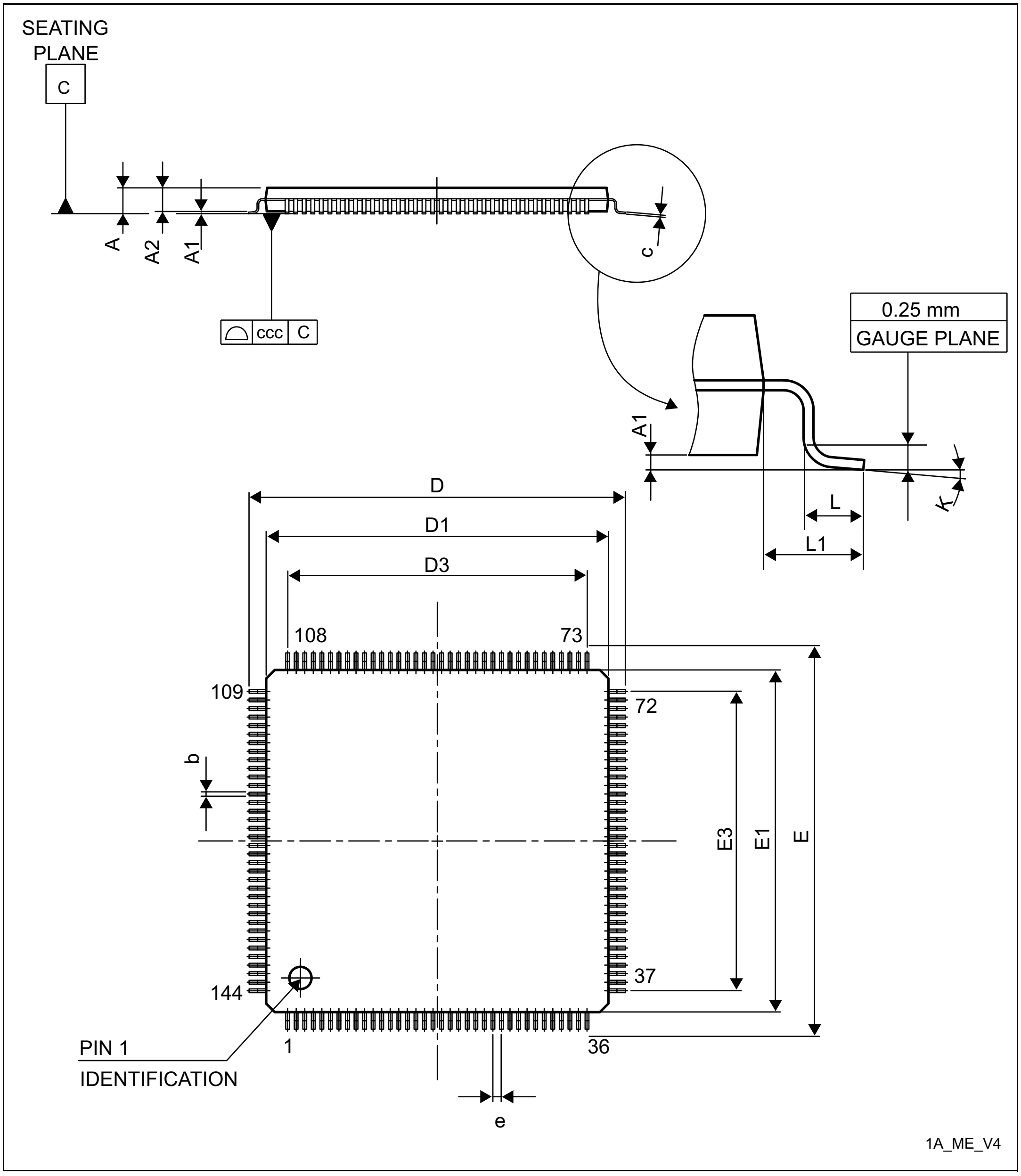


Table 77. Synchronous non-multiplexed NOR/PSRAM read timings[1][2]

Symbol	Parameter	Min	Max	Unit
$t_{w(CLK)}$	FSMC_CLK period	$2T_{HCLK}$	-	ns
$t_{d(CLKL-NExL)}$	FSMC_CLK low to FSMC_NEx low (x=0..2)	-	0	ns
$t_{d(CLKL-NExH)}$	FSMC_CLK low to FSMC_NEx high (x= 0…2)	1	-	ns
$t_{d(CLKL-NADVL)}$	FSMC_CLK low to FSMC_NADV low	-	2.5	ns

7.3 LQFP144 package information

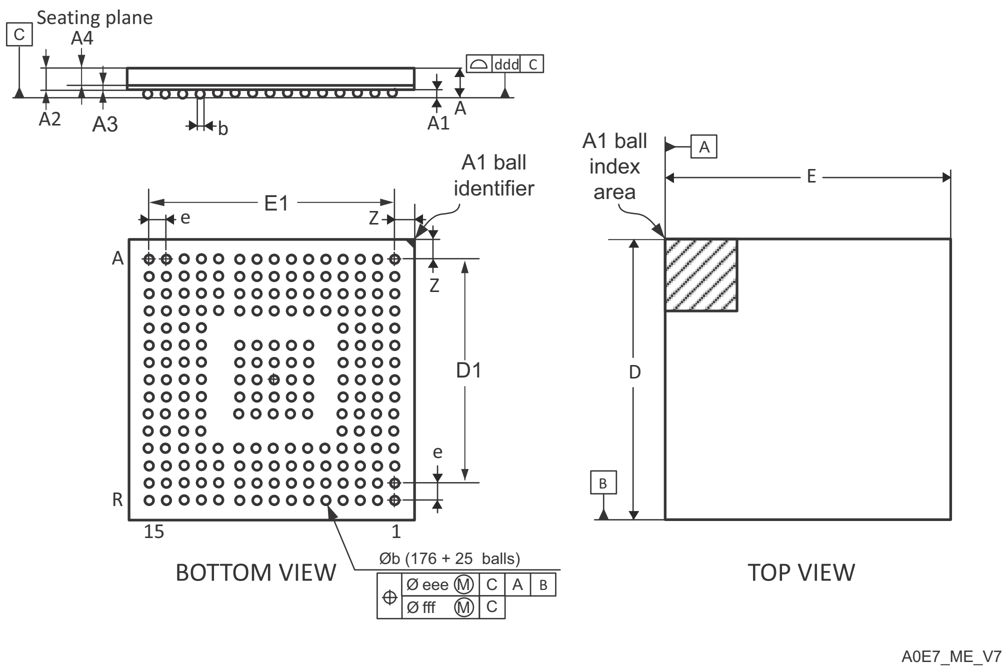
Figure 80. LQFP144 - 144-pin, 20 x 20 mm low-profile quad flat package outline



1. Drawing is not to scale.

7.5 UFBGA176+25 package information

Figure 85. UFBGA176+25 - 201-ball, 10 x 10 mm, 0.65 mm pitch, ultra fine pitch ball grid array package outline



1. Drawing is not to scale.

Table 90. UFBGA176+25, - 201-ball, 10 x 10 mm, 0.65 mm pitch, ultra fine pitch ball grid array package mechanical data

Symbol	millimeters			inches(1)		
	Min	Typ	Max	Min	Typ	Max
A	-	-	0.600	-	-	0.0236
A1	-	-	0.110	-	-	0.0043
A2	-	0.450	-	-	0.0177	-
A3	-	0.130	-	-	0.0051	0.0094
A4	-	0.320	-	-	0.0126	-
b	0.240	0.290	0.340	0.0094	0.0114	0.0134
D	9.850	10.000	10.150	0.3878	0.3937	0.3996
D1	-	9.100	-	-	0.3583	-
E	9.850	10.000	10.150	0.3878	0.3937	0.3996
E1	-	9.100	-	-	0.3583	-
e	-	0.650	-	-	0.0256	-
Z	-	0.450	-	-	0.0177	-
ddd	-	-	0.080	-	-	0.0031

Table 90. UFBGA176+25, - 201-ball, 10 x 10 mm, 0.65 mm pitch, ultra fine pitch ball grid array package mechanical data (continued)

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
eee	-	-	0.150	-	-	0.0059
fff	-	-	0.050	-	-	0.0020

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 86. UFBGA176+25 - 201-ball, 10 x 10 mm, 0.65 mm pitch, ultra fine pitch ball grid array package recommended footprint

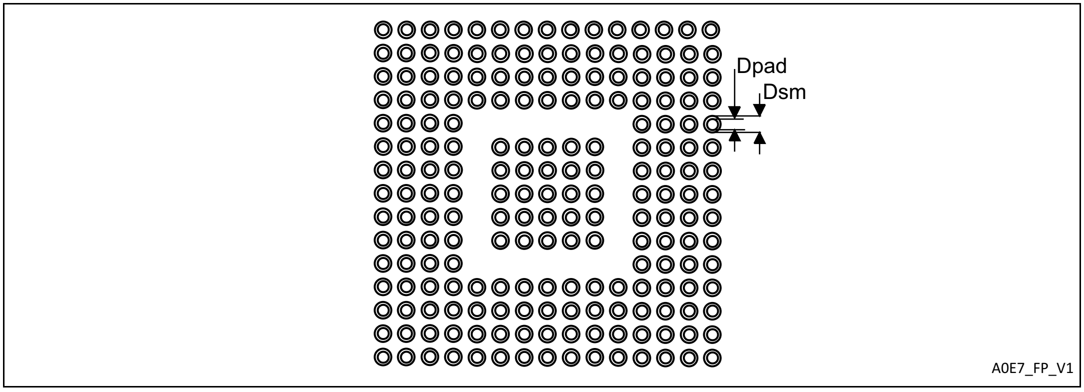
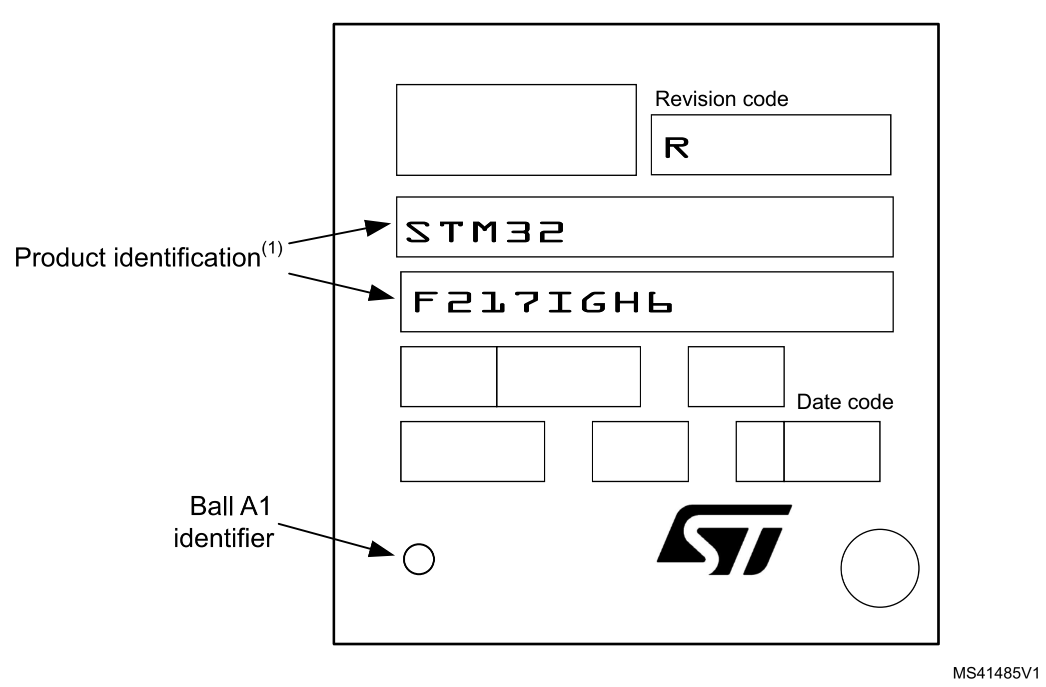


Table 91. UFBGA176+25 recommended PCB design rules (0.65 mm pitch BGA)

Dimension	Recommended values
Pitch	0.65 mm
Dpad	0.300 mm
Dsm	0.400 mm typ (depends on the soldermask registration tolerance)
Stencil opening	0.300 mm
Stencil thickness	Between 0.100 mm and 0.125 mm
Pad trace width	0.100 mm

Device marking

Figure 87. UFBGA176+25 marking (package top view)



1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

7.6 Thermal characteristics

The maximum chip-junction temperature, T_J max, in degrees Celsius, may be calculated using the following equation:

$$T_J \text{ max} = T_A \text{ max} + (P_D \text{ max x } \Theta_{JA})$$

Where:

- T_A max is the maximum ambient temperature in °C,
- Θ_{JA} is the package junction-to-ambient thermal resistance, in °C/W,
- P_D max is the sum of P_{INT} max and $P_{I/O}$ max (P_D max = P_{INT} max + $P_{I/O}$max),
- P_{INT} max is the product of I_{DD} and V_{DD}, expressed in Watts. This is the maximum chip internal power.

$P_{I/O}$ max represents the maximum power dissipation on output pins where:

$$P_{I/O} \text{ max} = \Sigma (V_{OL} \times I_{OL}) + \Sigma((V_{DD} - V_{OH}) \times I_{OH}),$$

taking into account the actual V_{OL} / I_{OL} and V_{OH} / I_{OH} of the I/Os at low and high level in the application.

Table 92. Package thermal characteristics

Symbol	Parameter	Value	Unit
Θ_{JA}	**Thermal resistance junction-ambient** LQFP 64 - 10 × 10 mm / 0.5 mm pitch	45	°C/W
	Thermal resistance junction-ambient LQFP100 - 14 × 14 mm / 0.5 mm pitch	46	
	Thermal resistance junction-ambient LQFP144 - 20 × 20 mm / 0.5 mm pitch	40	
	Thermal resistance junction-ambient LQFP176 - 24 × 24 mm / 0.5 mm pitch	38	
	Thermal resistance junction-ambient UFBGA176 - 10× 10 mm / 0.5 mm pitch	39	

Reference document

JESD51-2 Integrated Circuits Thermal Test Method Environment Conditions - Natural Convection (Still Air). Available from www.jedec.org.

8 Ordering information

Table 93. Ordering information scheme

Example: STM32 F 215 R E T 6 V xxx

Device family

STM32 = ARM-based 32-bit microcontroller

Product type

F = general-purpose

Device subfamily

215 = STM32F21x, connectivity, cryptographic acceleration

217= STM32F21x, connectivity, camera interface, cryptographic acceleration, Ethernet

Pin count

R = 64 pins

V = 100 pins

Z = 144 pins

I = 176 pins

Flash memory size

E = 512 Kbytes of Flash memory

G = 1024 Kbytes of Flash memory

Package

T = LQFP

H = UFBGA

Temperature range

6 = Industrial temperature range, –40 to 85 °C.

7 = Industrial temperature range, –40 to 105 °C.

Software option

Internal code or Blank

Options

xxx = programmed parts

TR = tape and reel

For a list of available options (speed, package, etc.) or for further information on any aspect of this device, contact your nearest ST sales office.

Table 94. Document revision history (continued)

Date	Revision	Changes
22-Apr-2011	4 (continued)	Updated $t_{res(TIM)}$ in *Table 49: Characteristics of TIMx connected to the APB1 domain*. Modified $t_{res(TIM)}$ and f_{EXT} *Table 50: Characteristics of TIMx connected to the APB2 domain*. Changed $t_{w(SCKH)}$ to $t_{w(SCLH)}$, $t_{w(SCKL)}$ to $t_{w(SCLL)}$, $t_{r(SCK)}$ to $t_{r(SCL)}$, and $t_{f(SCK)}$ to $t_{f(SCL)}$ in *Table 51: I2C characteristics* and *Figure 39: I2C bus AC waveforms and measurement circuit*. Added *Table 56: USB OTG FS DC electrical characteristics* and updated *Table 57: USB OTG FS electrical characteristics*. Updated V_{DD} minimum value in *Table 61: Ethernet DC electrical characteristics*. Updated *Table 65: ADC characteristics* and R_{AIN} equation. Updated R_{AIN} equation. Updated *Table 67: DAC characteristics*. Updated t_{START} in *Table 68: Temperature sensor characteristics*. Updated *Table 70: Embedded internal reference voltage*. Modified FSMC_NOE waveform in *Figure 55: Asynchronous non-multiplexed SRAM/PSRAM/NOR read waveforms*. Shifted end of FSMC_NEx/NADV/addresses/NWE/NOE/NWAIT of a half FSMC_CLK period, changed $t_{d(CLKH-NExH)}$ to $t_{d(CLKL-NExH)}$, $t_{d(CLKH-AIV)}$ to $t_{d(CLKL-AIV)}$, $t_{d(CLKH-NOEH)}$ to $t_{d(CLKL-NOEH)}$, and $t_{d(CLKH-NWEH)}$ to $t_{d(CLKL-NWEH)}$, and updated data latency from 1 to 0 in *Figure 59: Synchronous multiplexed NOR/PSRAM read timings*, *Figure 60: Synchronous multiplexed PSRAM write timings*, *Figure 61: Synchronous non-multiplexed NOR/PSRAM read timings*, and *Figure 62: Synchronous non-multiplexed PSRAM write timings*, Changed $t_{d(CLKH-NExH)}$ to $t_{d(CLKL-NExH)}$, $t_{d(CLKH-AIV)}$ to $t_{d(CLKL-AIV)}$, $t_{d(CLKH-NOEH)}$ to $t_{d(CLKL-NOEH)}$, $t_{d(CLKH-NWEH)}$ to $t_{d(CLKL-NWEH)}$, and modified $t_{w(CLK)}$ minimum value in *Table 75*, *Table 76*, *Table 77*, and *Table 78*. Updated R typical value in *Table 69: VBAT monitoring characteristics*.Updated note 2 in *Table 71*, *Table 72*, *Table 73*, *Table 74*, *Table 75*, *Table 76*, *Table 77*, and *Table 78*. Modified $t_{h(NIOWR-D)}$ in *Figure 68: PC Card/CompactFlash controller waveforms for I/O space write access*. Modified FSMC_NCEx signal in *Figure 69: NAND controller waveforms for read access*, *Figure 70: NAND controller waveforms for write access*, *Figure 71: NAND controller waveforms for common memory read access*, and *Figure 72: NAND controller waveforms for common memory write access*. Specified Full speed (FS) mode for *Figure 86: USB OTG HS peripheral-only connection in FS mode* and *Figure 87: USB OTG HS host-only connection in FS mode*.

Table 94. Document revision history (continued)

Date	Revision	Changes
20-Dec-2011	6 (continued)	Appendix *A.2: USB OTG full speed (FS) interface solutions*: updated *Figure 85: USB OTG FS (full speed) host-only connection* and added *Note 2*, updated *Figure 86: OTG FS (full speed) connection dual-role with internal PHY* and added *Note 3* and *Note 4*, modified *Figure 87: OTG HS (high speed) device connection, host and dual-role in high-speed mode with external PHY* and added *Note 2*. Appendix *A.3: USB OTG high speed (HS) interface solutions*: removed figures *USB OTG HS device-only connection in FS mode* and *USB OTG HS host-only connection in FS mode*, updated *Figure 87: OTG HS (high speed) device connection, host and dual-role in high-speed mode with external PHY*. Added Appendix *A.4: Ethernet interface solutions*. Updated disclaimer on last page.

Table 94. Document revision history (continued)

Date	Revision	Changes
29-Oct-2012	8 (continued)	Added *Figure 84: LQFP176 recommended footprint*. Added *Note 2* below *Figure 86: Regulator OFF/internal reset ON*. Updated device subfamily in *Table 93: Ordering information scheme*. Remove reference to note 2 for USB IOTG FS in *Table 93: Main applications versus package for STM32F2xxx microcontrollers*.
04-Nov-2013	9	Updated *Section 3.14: Power supply schemes*, *Section 3.15: Power supply supervisor*, *Section 3.16.1: Regulator ON* and *Section 3.16.2: Regulator OFF*. Added *Section 3.16.3: Regulator ON/OFF and internal reset ON/OFF availability*. Restructured RTC features and added reference clock detection in *Section 3.17: Real-time clock (RTC), backup SRAM and backup registers*. Added note indicating the package view below *Figure 9: STM32F21x LQFP64 pinout*, *Figure 10: STM32F21x LQFP100 pinout*, *Figure 11: STM32F21x LQFP144 pinout*, and *Figure 12: STM32F21x LQFP176 pinout*. Added *Table 6: Legend/abbreviations used in the pinout table*. *Table 7: STM32F21x pin and ball definitions*: content reformatted, removed indexes on V_{SS} and V_{DD}, updated PA4, PA5, PA6, PC4, BOOT0; replaced DCMI_12 by DCMI_D12, ETH_MII_RX_D0 by ETH_MII_RXD0, ETH_MII_RX_D1 by ETH_MII_RXD1, ETH_RMII_RX_D0 by ETH_RMII_RXD0, and ETH_RMII_RX_D1 by ETH_RMII_RXD1 in . *Table 9: Alternate function mapping*: replaced FSMC_BLN1 by FSMC_NBL1, added EVENTOUT as AF15 alternated function for PC13, PC14, PC15, PH0, PH1, and PI8. Updated *Figure 15: Pin loading conditions* and *Figure 16: Pin input voltage*. Added V_{IN} in *Table 13: General operating conditions*. Removed note applying to $V_{POR/PDR}$ minimum value in *Table 18: Embedded reset and power control block characteristics*. Updated notes related to C_{L1} and C_{L2} in *Section : Low-speed external clock generated from a crystal/ceramic resonator*. Updated conditions in *Table 40: EMS characteristics*. Updated *Table 41: EMI characteristics*. Updated V_{IL}, V_{IH} and V_{Hys} in *Table 45: I/O static characteristics*. Added *Section : Output driving current* and updated *Figure 37: I/O AC characteristics definition*. Updated $V_{IL(NRST)}$ and $V_{IH(NRST)}$ in *Table 48: NRST pin characteristics*, updated *Figure 37: I/O AC characteristics definition*. Removed tests conditions in *Section : I2C interface characteristics*. Updated *Table 51: I2C characteristics* and *Figure 39: I2C bus AC waveforms and measurement circuit*. Updated I_{VREF+} and I_{VDDA} in *Table 65: ADC characteristics*. Updated Offset comments in *Table 67: DAC characteristics*. Updated minimum $t_{h(CLKH-DV)}$ value in *Table 77: Synchronous non-multiplexed NOR/PSRAM read timings*.